

Die Size	7mil x 10 mil (180 ± 25um x 255 um ± 25um).
Die Thickness	3.9mil (100um ± 10um)
Bond pad diameter	P: 3mil (75um ± 10um) N: 3mil (75 ± 10um)
Electrode N Metal:	Au alloy
Electrode P Metal:	Au alloy

Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Condition	Rating	Unit
DC Forward Current	If	Ta=25°C	≤ 20	mA
DC Reverse Voltage	Vr	Ta=25°C	≤ 10	V
Junction Temperature	Tj	-	≤ 115	°C
Storage Temperature	Tstg	Chip	-40 ~ +85	°C
		Chip-on-tape/storage	5 ~ 35	
		Chip-on-tape/transportation	-20 ~ +65	
Temperature during packaging	-	-	280 (<10sec)	°C

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

Electro-Optical Characteristics: (Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
DC Forward Voltage	VF1	IF=10uA	1.3	-	-	V
	VF2	IF=20mA	1.8	-	2.5	V
DC Reverse Current	IR	VR=10V	-	-	5.0	µA
Domi. Wavelength*1	λd	IF=20mA	619	-	629	nm
Spectra Half-width	Δλ	IF=20mA	-	18	-	nm
Luminous Intensity*2,3	IV	E13	350	-	-	mcd
		E14	400	-	-	

*1: Basically, the wavelength span is 10nm; however, customers' special requirements are also welcome.

*2: Customers' special requirements are also welcome.

*3: Luminous intensity is measured by the manufacturer equipment on bare chips.

Typical Electro- Optical Characteristics Curve:

Fig.1 – Relative luminous Intensity vs. Forward Current

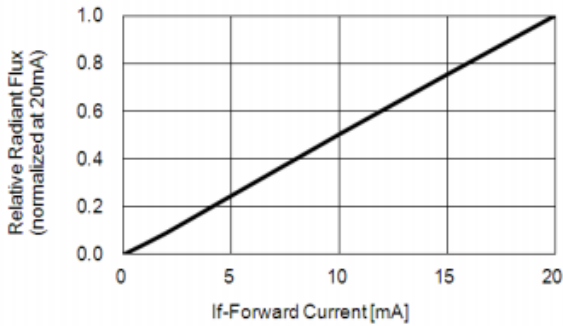


Fig.2 – Forward Current vs. Forward Voltage

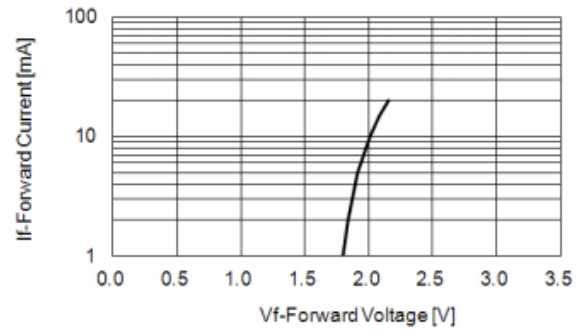


Fig.3 – Relative Intensity (@20mA) vs. Ambient Temperature

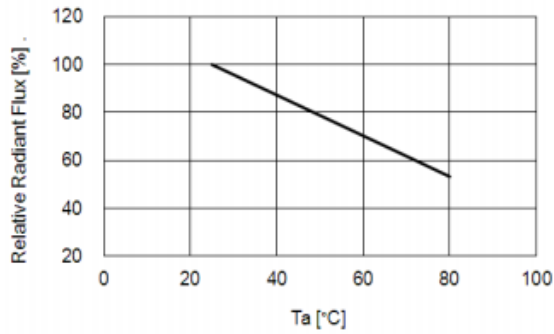


Fig.4 – Forward Voltage (@20mA) vs. Ambient Temperature

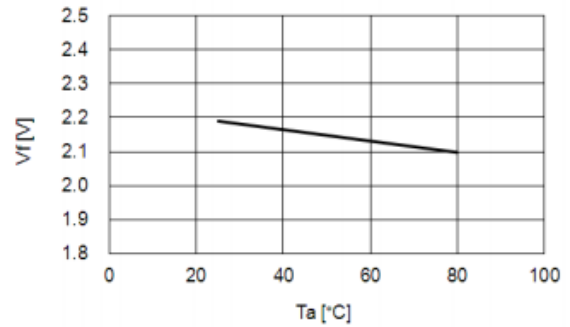


Fig.5 – Dominant Wavelength (@20mA) vs. Ambient Temperature

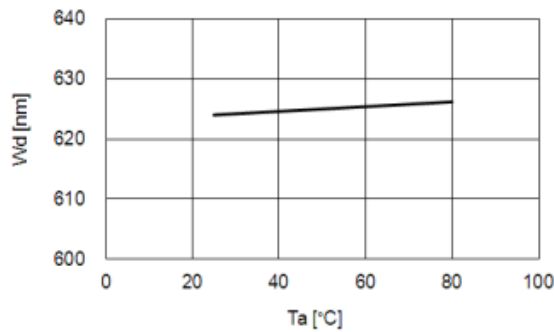


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 115°C)

